Description

The VSM110N02 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

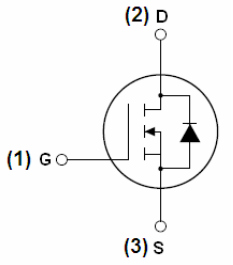
General Features

- V_{DS} =20V,I_D =110A
  $R_{DS(ON)}$ <4mΩ @ V_{GS}=10V (Typ3mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Load switching
- Uninterruptible power supply

TO-252



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM110N02-T2	VSM110N02	TO-252	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	110	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	77	A
Pulsed Drain Current	I_{DM}	200	A
Maximum Power Dissipation	P_D	85	W
Single pulse avalanche energy (Note 5)	E_{AS}	450	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	1.5	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

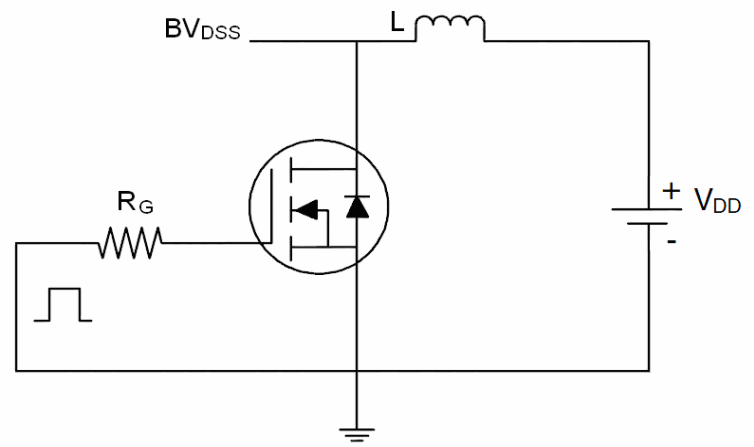
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=30A	-	3	4	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=30A	100	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz		3000		PF
Output Capacitance	C_{oss}			700		PF
Reverse Transfer Capacitance	C_{rss}			390		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	VGS=10V,VDS=10V RL=0. 5Ω,RGEN=3Ω	-	12.5	-	nS
Turn-on Rise Time	t_r		-	35.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	40	-	nS
Turn-Off Fall Time	t_f		-	32.5	-	nS
Total Gate Charge	Q_g	VGS=4.5V,VDS=10V,ID=30A		30.4		nC
Gate-Source Charge	Q_{gs}			9.5		nC
Gate-Drain Charge	Q_{gd}			19.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=20A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S	-	-	-	110	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 30A di/dt = 100A/μs (Note3)	-	35.3	-	nS
Reverse Recovery Charge	Qrr		-	30.7	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

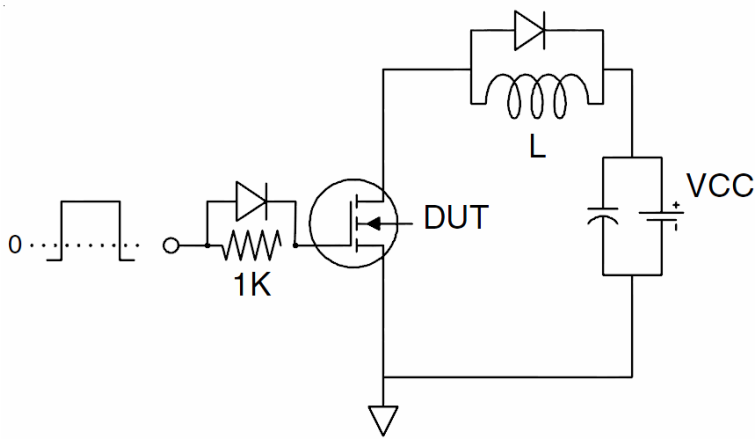
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition：Tj=25℃,V_{DD}=10V,V_G=10V,L=0.5mH,Rg=25Ω

Test circuit

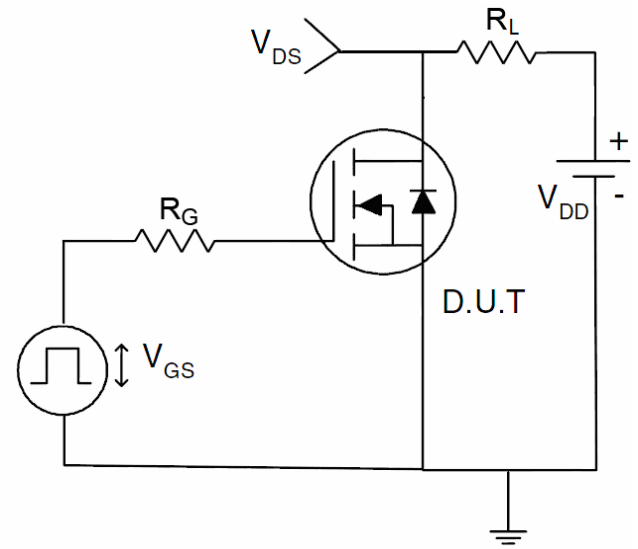
1）E_{AS} test Circuits



2）Gate charge test Circuit:



3）Switch Time Test Circuit：



Typical Electrical and Thermal Characteristics (Curves)

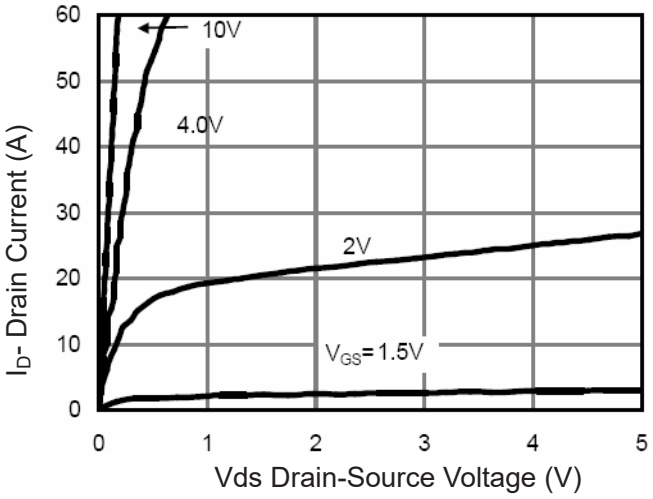


Figure 1 Output Characteristics

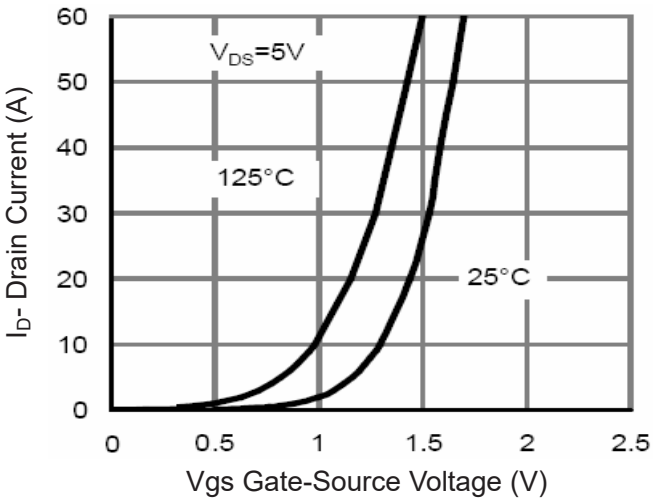


Figure 2 Transfer Characteristics

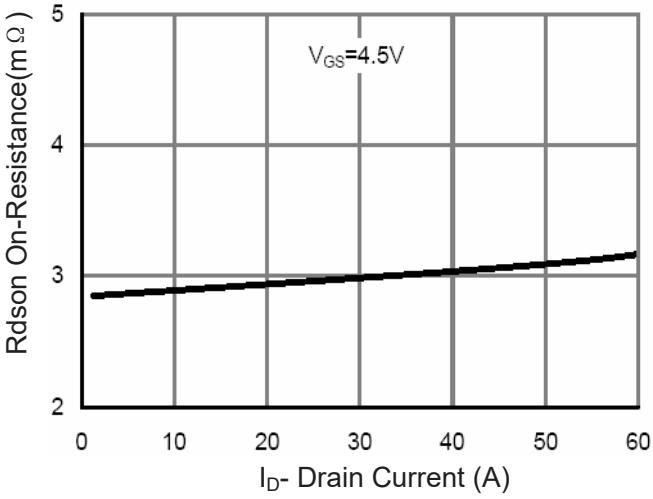


Figure 3 Rdson- Drain Current

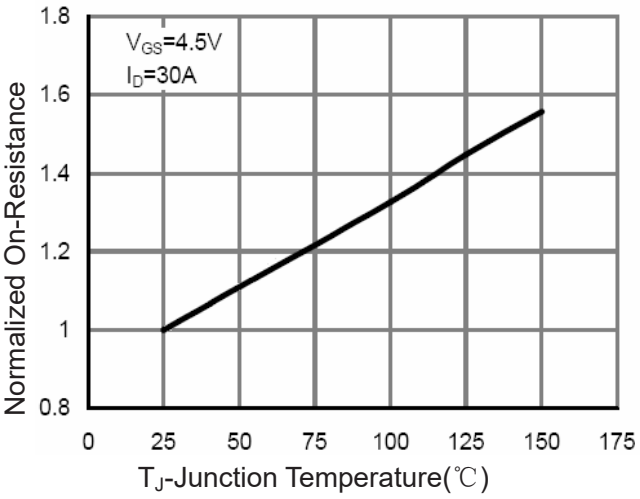


Figure 4 Rdson-Junction Temperature

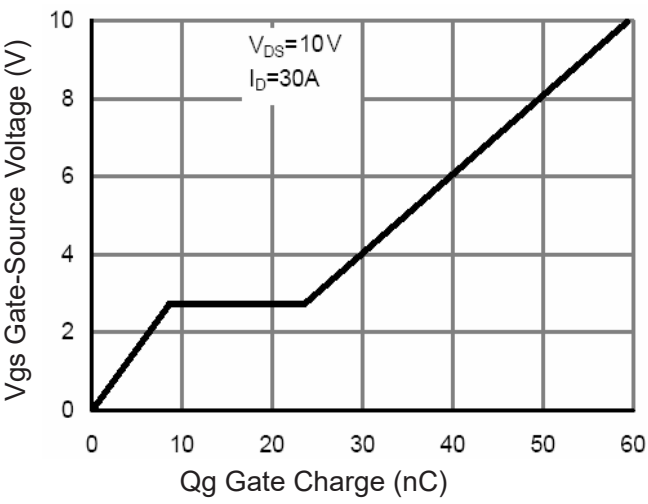


Figure 5 Gate Charge

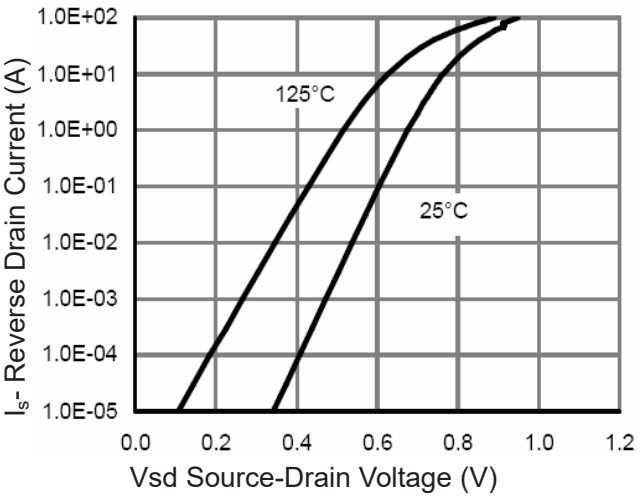


Figure 6 Source- Drain Diode Forward

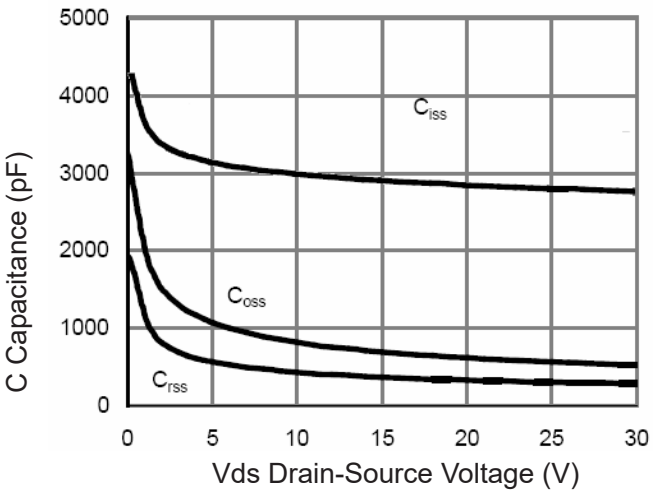


Figure 7 Capacitance vs Vds

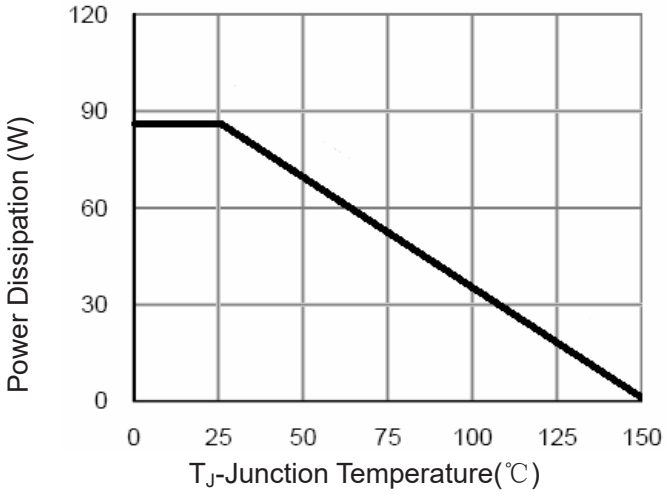


Figure 9 Power De-rating

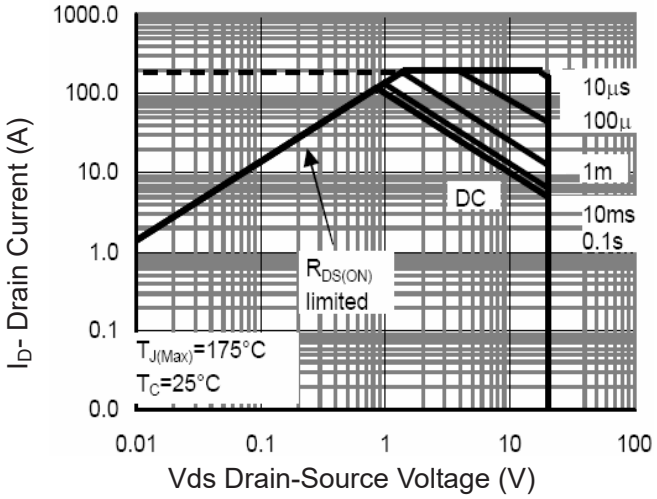


Figure 8 Safe Operation Area

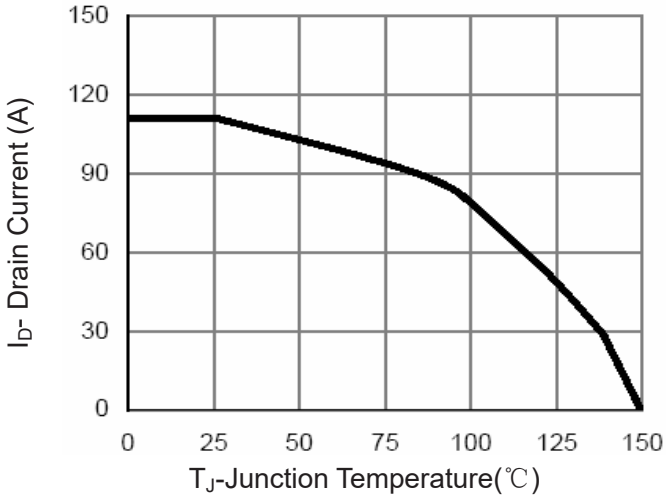


Figure 10 Current De-rating

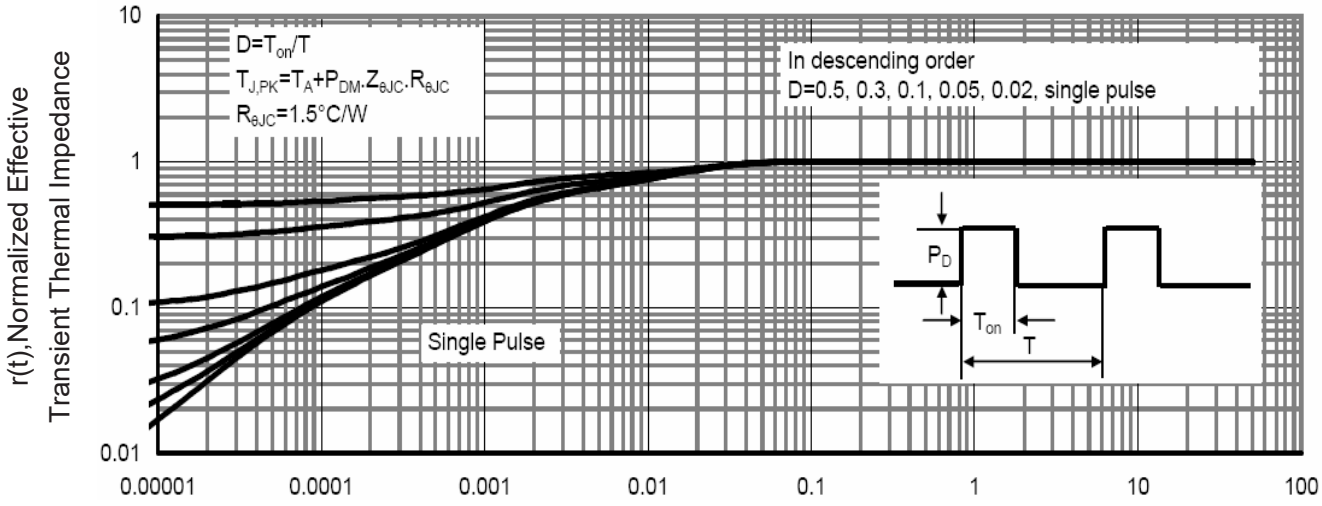


Figure 11 Normalized Maximum Transient Thermal Impedance